

PCN# : P642AAB Issue Date : Apr. 12, 2016

Information Only Notification

This is to inform you that a change is being made to the following products.

This is a minor change that has no impact on product quality, reliability, electrical or mechanical performance. Affected products will remain fully compliant to all published specifications. Notification is being made for informational purposes only and there is no approval required. Products incorporating this change may be shipped interchangeably with existing unchanged products on or after the issue date of this notification.

Please contact your local Customer Quality Engineer if you have any questions regarding this notification.

Implementation of change:

Description of Change (From) :

1) Features: Typical Qg(tot) = 71 nC at VGS = 10V, ID = 80 A (page 1)

2) Highlighted items from Electrical Characteristics table (see attachment)

Ciss	Input Capacitance	N 2511 N		-	5120	-	pF
Coss	Output Capacitance	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz		-	1450	-	pF
Crss	Reverse Transfer Capacitance	1 - 10012		-	88	-	pF
Rg	Gate Resistance	f = 1MHz			2.8	-	Ω
Q _{g(ToT)}	Total Gate Charge	V _{GS} = 0 to 10V	V _{DD} = 32V	-	71	92	nC
Q _{g(th)}	Threshold Gate Charge	V _{GS} = 0 to 2V	I _D = 80A	-	9.5	-	nC
Qgs	Gate-to-Source Gate Charge		_	-	25	-	nC
Qgd	Gate-to-Drain "Miller" Charge			-	13	-	nC

Dynamic Characteristics

Switching Characteristics

ton	Turn-On Time		-	-	62	ns
t _{d(on)}	Turn-On Delay		-	22	-	ns
t _r	Rise Time	V _{DD} = 20V, I _D = 80A,	-	24	-	ns
t _{d(off)}	Turn-Off Delay	V _{GS} = 10V, R _{GEN} = 6Ω	-	39	-	ns
4	Fall Time]	-	19	-	ns
toff	Turn-Off Time		-	-	81	ns

Drain-Source Diode Characteristics

V	Source-to-Drain Diode Voltage	I _{SD} =80A, V _{GS} = 0V	-	-	1.25	V
VSD	Source-to-brain blode volage	I _{SD} = 40A, V _{GS} = 0V	-	-	1.2	V
t _m	Reverse-Recovery Time	I _F = 80A, dI _{SD} /dt = 100A/µs	-	74	<mark>95</mark>	ns
Qrr	Reverse-Recovery Charge	V _{DD} = 32V	-	85	110	nC

Note:

4: The maximum value is specified by design at T_J = 175°C. Product is not tested to this condition in production.

Description of Change (To) :

1) Features: Typical Qg(tot) = 68 nC at VGS = 10V, ID = 80 A (page 1)

2) Highlighted items updated in Electrical Characteristics table (see attachment)

Dynamic Characteristics

Ciss	Input Capacitance	V - 2004 M	ob /	-	5150	-	pF
Coss	Output Capacitance	$v_{DS} = 20V, v_{GS} =$ f = 1MHz	$V_{DS} = 20V, V_{GS} = 0V,$ f = 1MHz		1770	-	pF
Crss	Reverse Transfer Capacitance	1 - 11112		-	89	-	pF
Rg	Gate Resistance	f = 1MHz	f = 1MHz		2.8	-	Ω
Q _{g(ToT)}	Total Gate Charge	V _{GS} = 0 to 10V	V _{DD} = 32V	-	68	92	nC
Q _{g(th)}	Threshold Gate Charge	V _{GS} = 0 to 2V	I _D = 80A	-	9.3	14	nC
Qgs	Gate-to-Source Gate Charge			-	22	-	nC
Q _{gs} Q _{gd}	Gate-to-Drain "Miller" Charge			-	12	-	nC

Switching Characteristics

ton	Turn-On Time		-	-	<mark>51</mark>	ns
t _{d(on)}	Turn-On Delay		-	19	-	ns
t,	Rise Time	V _{DD} = 20V, I _D = 80A, V _{GS} = 10V, R _{GEN} = 6Ω	-	20	-	ns
t _{d(off)}	Turn-Off Delay		-	<mark>41</mark>	-	ns
t _e	Fall Time			19	-	ns
tom	Turn-Off Time		-	-	79	ns

Drain-Source Diode Characteristics

V	Source-to-Drain Diode Voltage	I _{SD} =80A, V _{GS} = 0V	-	-	1.25	V
VSD	Source-to-brain blode voltage	I _{SD} = 40A, V _{GS} = 0V	-	-	1.2	V
t _{rr}	Reverse-Recovery Time	I _F = 80A, dI _{SD} /dt = 100A/μs	-	74	96	ns
Qrr	Reverse-Recovery Charge	V _{DD} = 32V		83	108	nC

Note:

4: The maximum value is specified by design at T_J = 175°C. Product is not tested to this condition in production.

Reason for Change: This is a datasheet change only.

Parameters updated per re-characterization test results.



Affected Product(s):

FDMS9408_F085	



Appendix A: Changed Products

D

PCN Number : P642AAB

С

Product	Customer Part Number	BBB	Drawing
FDMS9408_F085		Y	Ν